

In Application of: Wolfgang M.J. Hofmann and)
Noel C. MacDonald)
)
Application No. Division of 10/021,311) Group:
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Filed: Even date herewith) Examiner:
)
For: MULTIPLE-LEVEL ACTUATORS)
AND CLAMPING DEVICES)

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October 7, 2003

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U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	T, B, A.
				Filing Date	Even Date Herewith
				First Named Inventor	Wolfgang M.J. Hofmann
				Group Art Unit	1772
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	Hofmann

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		CHANG, T.H.P.k Kern, D.P., Muray, L.P.; Microminiaturization of electron optical systems; J. Vacuum Science & Technology B, vol. 8, pp. 1698-1705, 1990	
		CHANG, T.H.P., Kern, D.P., McCord, M.A., Muray, L.P.; A Scanning Tunneling Microscope Controlled Field Emission Microprobe System; J. Vacuum Science & Technology, vol. 9, pp. 438-443, 1991	
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		MACDONALD, N.C.; SCREAM Microelectromechanical systems; Microelectronic Engineering, vol. 32, pp. 49-73, Sept. 1996	
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